UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,953,375 B2 Page 1 of 2

APPLICATION NO.: 10/813204 DATED: October 11, 2005

INVENTOR(S) : Kie Y. Ahn and Leonard Forbes

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column, Line	Reads	Should Read
Item (56), Other Publications, Stevenson Reference	"of SiO ₂ , Films Over"	of SiO ₂ Films Over
Item (56), Other Publications, Vaudaine Reference	"technical digest of IEDM 91,"	Technical Digest of IEDM 91,
Column 4, Line 32	"FIG. 3), having a"	FIG. 3) having a
Column 5, Line 18	"ca. 10 ²⁻¹⁰³ "	ca. 10^2 - 10^3
Column 6, Line 35	"Mater. Sci. 32, (1997),"	Mater. Sci. 32 (1997),
Column 7, Line 23	"69(7), (1996),"	69(7) (1996)
Column 7, Line 38	"Silicon at low"	Silicon at Low
Column 7, Line 53	"Part 1, Vol. 36,"	Part I, Vol. 36,
Column 9, Lines 24-25	"comprises chemical- mechanical polishing the porous"	comprises chemical- mechanical polishing of the porous
Column 10, Lines 26-27	"comprises chemical- mechanical polishing the porous"	comprises chemical- mechanical polishing of the porous
Column 10, Line 41	"act of fanning"	act of forming

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Column, Line

Reads

Should Read

Column 12, Lines 10-11

"comprises chemical-

mechanical polishing the"

--comprises chemicalmechanical polishing of

Signed and Sealed this

Eighteenth Day of September, 2007

JON W. DUDAS Director of the United States Patent and Trademark Office